Advanced PECVD-LS Nitride2(n=1.93,-40MPa, 8.3nm/min)				Advanced PECVD LS SiN~2500A Typical Film Properties
SiN depostion~2500A, 300C				Deposition rate=4.33nm/min
Step1:	NITRIDE2 coat			Refractive index@632.8nm=1.932
	Name	Value	Changeable	Stress=-26.31MPa
	LF on time(ms)	1000ms	Y	
	LF setpoint	90W	Y	
	Process pressure	800 mtorr	N	HF etch rate=46.22nm/min
	RF on time(ms)	6000ms	N	
	RF setpoint	30 W	N	
	stabilization time	15 seconds	N	
	step time(m)	**10 min**	**Y**	
	step time(s)	**0 sec**	**Y**	
	2%SiH4 %He	1040sccm	N	
	N2	980sccm	N	
	NH3	18sccm	N	
Step2:	NITRIDE2 deposition			
	Name	Value	Changeable	
	LF on time(ms)	1000ms	Y	
	LF setpoint	90W	Y	
	Process pressure	800 mtorr	N	
	RF on time(ms)	6000ms	N	
	RF setpoint	30 W	N	
	stabilization time	15 seconds	N	
	step time(m)	**30 min**	**Y**	
	step time(s)	**0 sec**	**Y**	
	2%SiH4 %He	1040sccm	N	
	N2	980sccm	N	
	NH3	18sccm	N	
Step3: STANDARD PLASMA CLEAN				
	1. pump down			
	Name	Value	Changeable	
	stabilization time	15 seconds	N	
	step time(m)	0	N	
	step time(s)	30	N	
	2. Pre-purge			
	Name	Value	Changeable	
	purge	**1 (Yes/No)**	N	
	stabilization time	15 seconds	N	
	step time(m)	**1**	**N**	
	step time(sec)	0	N	
	3.1 High Pressure			
	Name	Value	Changeable	
	Cload position	**50%**	**N**	
	Ctune position	**50%**	**N**	
	DriveMatch	**1 (Yes/No)**	**N**	
	Process pressure	600 mtorr	N	
	RF setpoint=300	300 W	N	
	Stabilization time	35 seconds	N	
	step time(m)	**ENTER TIME**	Y	**For 7min(coat+deposition) run 1min CLEAN**
	step time(s)	0	Y	
	CF4/O2(5)	500 sccm	N	